

SBR40U150CT - Prel SBR40U150CTF - Prel SBR40U150CTI - Prel SBR40U150CTB - Prel

Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
I _{F(AV)} Rectangular Waveform	40	Α
V_{RRM}	150	V
V _F @20A, Tj=125 ^O C	0.73	V, typ
Tj (operating/storage)	-65 to 175	°C

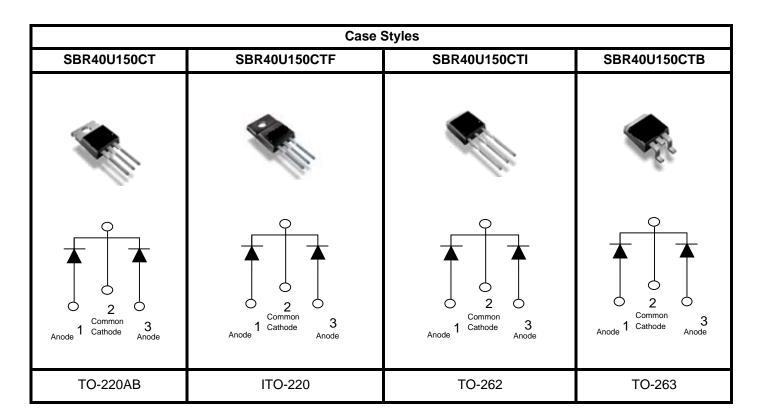
Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

ELECTRICAL:

- * Ultra-Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 175°C Operating Junction Temperature

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages





SBR40U150CT - Prel SBR40U150CTF - Prel SBR40U150CTI - Prel SBR40U150CTB - Prel

Maximum Ratings and Electrical Characteristics (at 25°C unless otherwise specified) SYMBOL **UNITS** DC Blocking Voltage V_{RM} Working Peak Reverse Voltage 150 Volts V_{RWM} Peak Repetitive Reverse Voltage V_{RRM} Average Rectified Forward Current (Rated V_R-20Khz Square Wave) - 50% duty 40 I_{\circ} **Amps** Peak Forward Surge Current - 1/2 60hz \mathbf{I}_{FSM} 300 **Amps** Peak Repetitive Reverse Surge Current 3 **Amps** I_{RRM} (2uS-1Khz) Instantaneous Forward Voltage (per leg) Max Typ $I_{\rm F} = 20A; T_{\rm I} = 25^{\circ}C$ ٧ 0.80 Volts $I_F = 20A; T_J = 125^{\circ}C$ 0.76 Maximum Instantaneous Reverse Current at Max Typ Rated V_{RM} 0.5 I_R mΑ $T_1 = 25^{\circ}C$ 25 mΑ $T_{J} = 125^{\circ}C$ Maximum Rate of Voltage Change dv/dt 10,000 V/uS (at Rated V_R)

Package = ITO-220

Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263

Operating and Storage Junction Temperature

APD SEMICONDUCTOR reserves the right to make changes without further notice to any products herein. APD SEMICONDUCTOR makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APD SEMICONDUCTOR assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APD SEMICONDUCTOR data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APD SEMICONDUCTOR does not convey any license under its patent rights nor the rights of others. APD SEMICONDUCTOR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APD SEMICONDUCTOR product could create a situation where personal injury or death may occur. Should Buyer purchase or use APD SEMICONDUCTOR products for any such unintended or unauthorized application, Buyer shall indemnify and hold APD SEMICONDUCTOR and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APD SEMICONDUCTOR was negligent regarding the design or manufacture of the part.

 $R\theta_{JC}$

 $T_{\rm J}$

APD Semiconductor, Inc.

1 Lagoon Drive, Suite 410, Redwood City, CA 94065, USA Ph: 650 508 8896 FAX: 650 508 8865 Homepage: www.apdsemi.com email: info@apdsemi.com

2

-65 to +175

°C/W

οС

^{*} Pulse width < 300 uS, Duty cycle < 2%